

REMARKS

Claims 49-54 are canceled. New claims 69-72 are added. No new matter is added as the originally-filed application supports the new claims at, for example, page 15 and Figs. 20-21. Claims 69-72 are pending in the application.

The Examiner states the title is not descriptive (pg. 2 of paper no. 9). The title is amended, and as amended, is descriptive of the invention.

Claims 49-54 stand rejected under 35 U.S.C. §102(e) as being anticipated by Lin et al. (U.S. Patent No. 6,153,478).

New claim 69 recites an insulative material filling a trench and having a portion outward of the trench and semiconductor substrate, the portion comprising an outermost upper surface elevationally above an uppermost surface of an oxide layer and sidewalls connecting the outermost upper surface with the oxide layer, the connection between the sidewalls and the outermost upper surface comprising curved corners, and the connection between the sidewalls and the oxide layer comprising curved corners extending from elevationally above the oxide layer downward to the uppermost surface of the oxide layer. Lin teaches a filling layer 44 having a portion outward of the trench and semiconductor substrate 30, the portion comprising an upper surface elevationally above an oxide layer 32a and sidewalls connecting the upper surface of filling layer 44 with the oxide layer 32a (Fig. 8). However, Lin teaches the connection between the sidewalls of the portion of the filling layer 44 and the upper surface of the filling layer 44 comprise **pointed** corners (Fig. 8), and not curved corners as recited in claim 69.

Accordingly, in no fair or reasonable interpretation does Lin, singularly or in any combination, teach the connection between the sidewalls (of the portion of the insulative material) and the outermost upper surface (of the portion of the insulative material) comprises curved corners as recited in claim 69. Accordingly, Lin, singularly or in any combination, fails to teach or suggest a positively recited limitation of claim 69, and therefore, claim 69 is allowable.

Moreover, Lin teaches the connection between the sidewalls of the filling layer 44 and the oxide layer 32a comprises **pointed** corners (Fig. 8), and not curved corners as recited in claim 69. For this additional reason, Lin, singularly or in any combination, fails to teach or suggest another positively recited limitation of claim 69, and therefore, claim 69 is allowable for this additional reason. Applicant respectfully requests allowance of claim 69 in the next office action.

Claims 70-72 depend from independent claim 69, and therefore, are allowable for the reasons discussed above with respect to the independent claim, as well as for their own recited features which are not shown or taught by the art of record.

Further, Applicant herewith submits a duplicate copy of the Information Disclosure Statement and Form PTO-1449s filed together with this application on February 8, 2002. No initialed copy of the PTO-1449s have been received back from the Examiner. To the extent that the submitted references listed on the Form PTO-1449s have not already been considered, and the Form PTO-1449s have not been initialed with a copy being returned to Applicant, such examination

and initialing are requested at this time, as well as return of a copy of the initialed Form PTO-1449s to the undersigned.

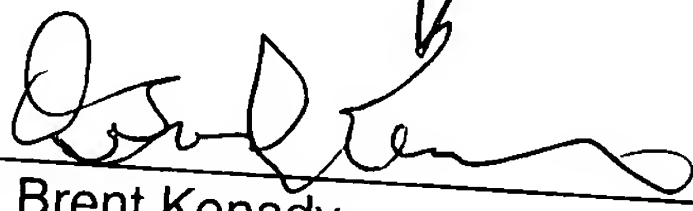
Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) are captioned "**A Version with markings to show changes made.**"

In view of the foregoing, allowance of claims 49-54 is requested. This application is now believed to be in immediate condition for allowance, and action to that end is respectfully requested. If the Examiner's next anticipated action is to be anything other than a Notice of Allowance, the undersigned respectfully requests a telephone interview prior to issuance of any such subsequent action.

Respectfully submitted,

Dated: 12-27-02

By:


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 10/071,456
Filing Date February 8, 2002
Inventor David L. Dickerson et al.
Assignee Micron Technology, Inc.
Group Art Unit 2814
Examiner A.D. Mai
Attorney's Docket No. MI22-1943
Title: Semiconductor Constructions (As Amended)

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE
ACCOMPANYING RESPONSE TO AUGUST 27, 2002 OFFICE ACTION**

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

In the Title

On page 1, the Title has been amended as shown below:

~~Isolation Region Forming Methods~~ Semiconductor Constructions

In the Specification

At page 1, the paragraph inserted before the "Technical Field" by the amendment dated February 8, 2002, has been amended as shown below:

RELATED PATENT DATA

This patent resulted from a Continuation Application of U.S. Patent Application Serial No. 09/146,838, filed September 3, 1998, now U.S. Patent No.

6,478,978 B1, entitled "Isolation Region Forming Methods" the disclosure of which is incorporated by reference.

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 29-54 are canceled.

New claims 69-72 are added.

END OF DOCUMENT